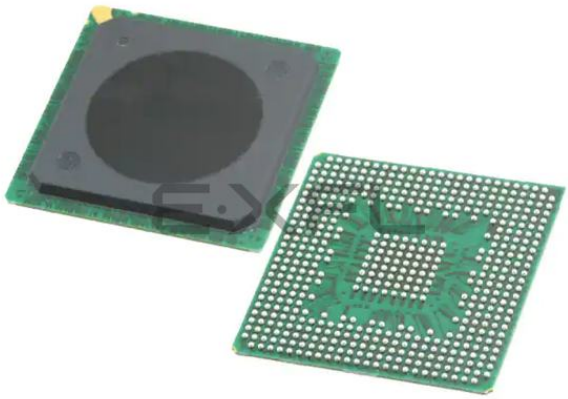

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Details	
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Core Size	32-Bit Single-Core
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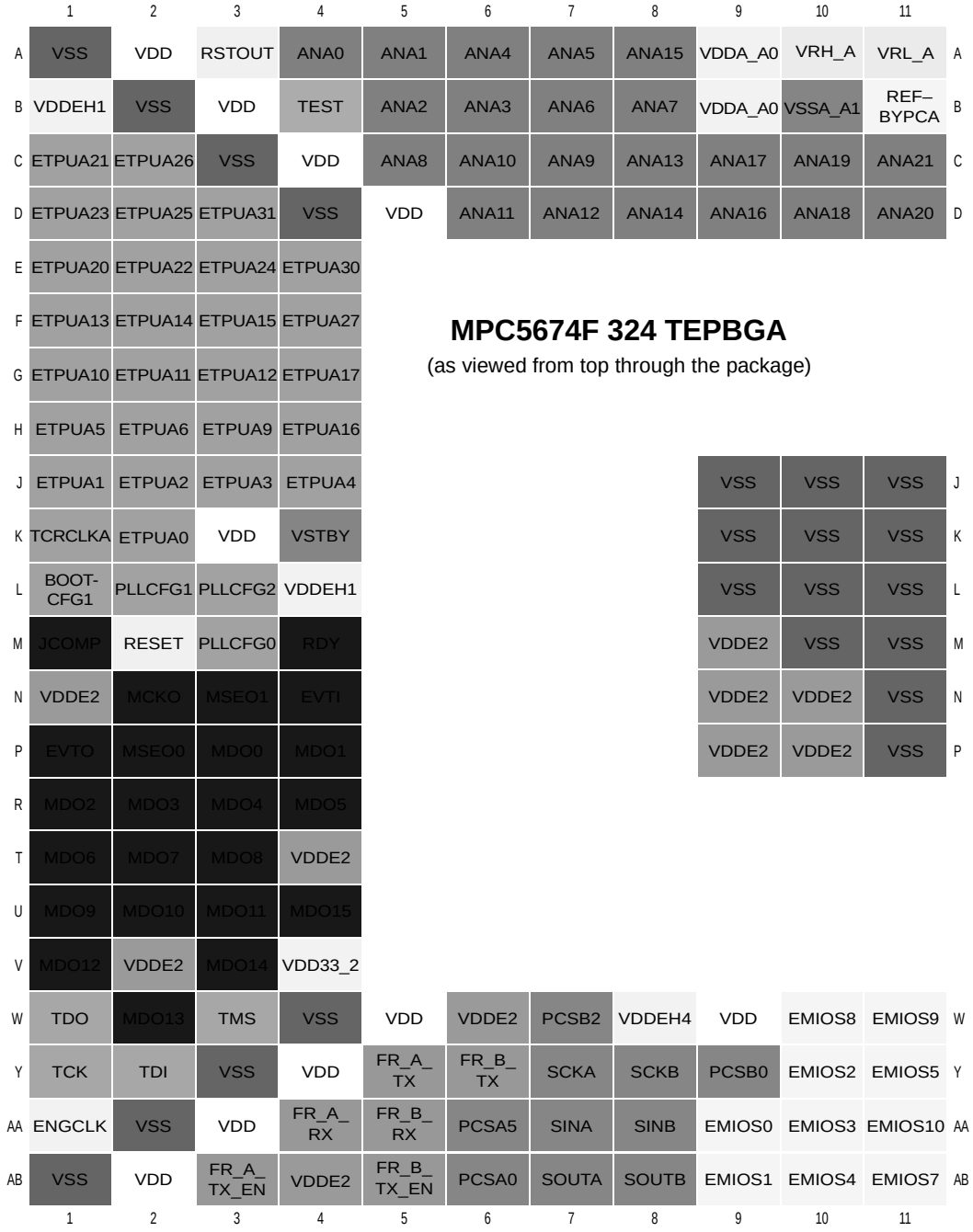
Peripherals	DMA, POR, PWM
Number of I/O	32
Program Memory Size	3MB (3M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	1.08V ~ 5.25V
Data Converters	A/D 64x12b
Oscillator Type	External
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	516-BBGA
Supplier Device Package	516-PBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5673ff3mvy2



	1	2	3	4	5	6	7	8	9	10	11	
A	VSS	VDD	RSTOUT	ANA0	ANA1	ANA4	ANA5	ANA15	VDDA_A0	VRH_A	VRL_A	A
B	VDDEH1	VSS	VDD	TEST	ANA2	ANA3	ANA6	ANA7	VDDA_A0	VSSA_A1	REF–BYPCA	B
C	ETPUA21	ETPUA26	VSS	VDD	ANA8	ANA10	ANA9	ANA13	ANA17	ANA19	ANA21	C
D	ETPUA23	ETPUA25	ETPUA31	VSS	VDD	ANA11	ANA12	ANA14	ANA16	ANA18	ANA20	D
E	ETPUA20	ETPUA22	ETPUA24	ETPUA30								E
F	ETPUA13	ETPUA14	ETPUA15	ETPUA27								F
G	ETPUA10	ETPUA11	ETPUA12	ETPUA17								G
H	ETPUA5	ETPUA6	ETPUA9	ETPUA16								H
J	ETPUA1	ETPUA2	ETPUA3	ETPUA4					VSS	VSS	VSS	J
K	TCRCLKA	ETPUA0	VDD	VSTBY					VSS	VSS	VSS	K
L	BOOT-CFG1	PLLCFG1	PLLCFG2	VDDEH1					VSS	VSS	VSS	L
M	JCOMP	RESET	PLLCFG0	RDY					VDDE2	VSS	VSS	M
N	VDDE2	MCKO	MSEO1	EVTI					VDDE2	VDDE2	VSS	N
P	EVTO	MSEO0	MDO0	MDO1					VDDE2	VDDE2	VSS	P
R	MDO2	MDO3	MDO4	MDO5								R
T	MDO6	MDO7	MDO8	VDDE2								T
U	MDO9	MDO10	MDO11	MDO15								U
V	MDO12	VDDE2	MDO14	VDD33_2								V
W	TDO	MDO13	TMS	VSS	VDD	VDDE2	PCSB2	VDDEH4	VDD	EMIOS8	EMIOS9	W
Y	TCK	TDI	VSS	VDD	FR_A_TX	FR_B_TX	SCKA	SCKB	PCSB0	EMIOS2	EMIOS5	Y
AA	ENGCLK	VSS	VDD	FR_A_RX	FR_B_RX	PCSA5	SINA	SINB	EMIOS0	EMIOS3	EMIOS10	AA
AB	VSS	VDD	FR_A_TX_EN	VDDE2	FR_B_TX_EN	PCSA0	SOUTA	SOUTB	EMIOS1	EMIOS4	EMIOS7	AB
	1	2	3	4	5	6	7	8	9	10	11	

Figure 4. MPC5674F 324-ball TEPBGA (1 of 2)

3.2 416-ball TEPBGA Pin Assignments

Figure 6 shows the 416-ball TEPBGA pin assignments in one figure. The same information is shown in Figure 7 through Figure 10.

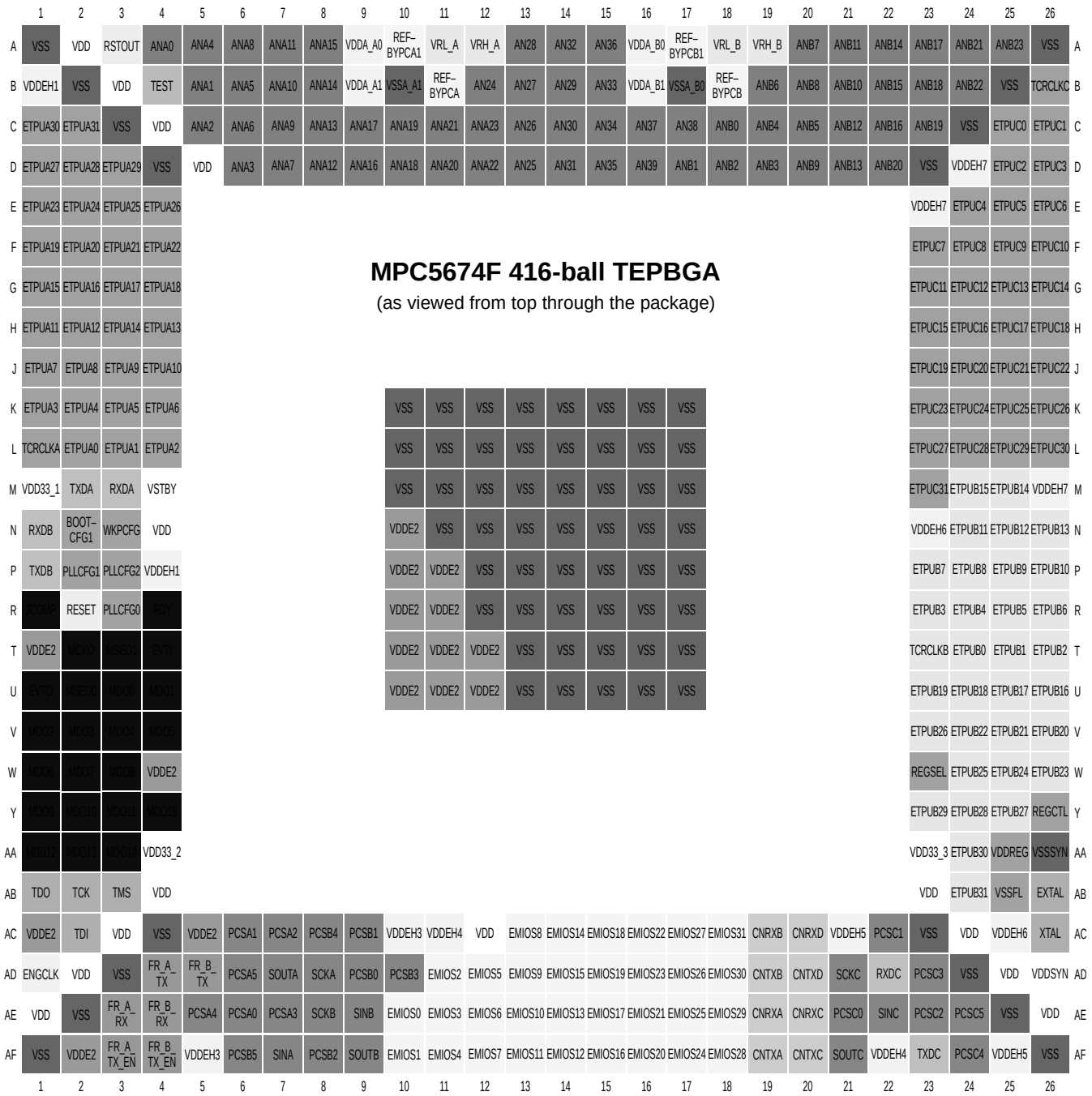


Figure 6. MPC5674F 416-ball TEPBGA (full diagram)

Table 5. Thermal Characteristics, 516-pin TEPBGA Package[1]

Characteristic	Symbol	Value	Unit
Junction to Ambient [2,3] Natural Convection (Single layer board)	$R_{\theta JA}$	25	°C/W
Junction to Ambient [2,4] Natural Convection (Four layer board 2s2p)	$R_{\theta JA}$	18	°C/W
Junction to Ambient (@200 ft./min., Single layer board)	$R_{\theta JMA}$	20	°C/W
Junction to Ambient (@200 ft./min., Four layer board 2s2p)	$R_{\theta JMA}$	15	°C/W
Junction to Board [5]	$R_{\theta JB}$	10	°C/W
Junction to Case [6]	$R_{\theta JC}$	6	°C/W
Junction to Package Top [7] Natural Convection	Ψ_{JT}	2	°C/W

1 Thermal characteristics are targets based on simulation that are subject to change per device characterization. This data is PRELIMINARY based on similar package used on other devices.

2 Junction temperature is a function of on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

3 Per JEDEC JESD51-2 with the single layer board horizontal. Board meets JESD51-9 specification.

4 Per JEDEC JESD51-6 with the board horizontal.

5 Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.

6 Indicates the average thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1) with the cold plate temperature used for the case temperature.

7 Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2.

Table 6. Thermal Characteristics, 324-pin Package[1]

MPC5674F Thermal Characteristic	Symbol	Value	Unit
Junction to ambient [2, 3], natural convection (one-layer board)	$R_{\theta JA}$	29	°C/W
Junction to ambient [1, 4], natural convection (four-layer board 2s2p)	$R_{\theta JA}$	19	°C/W
Junction to ambient (@200 ft./min., one-layer board)	$R_{\theta JMA}$	23	°C/W
Junction to ambient (@200 ft./min., four-layer board 2s2p)	$R_{\theta JMA}$	16	°C/W
Junction to board [5] (four-layer board 2s2p)	$R_{\theta JB}$	10	°C/W
Junction to case [6]	$R_{\theta JC}$	7	°C/W
Junction to package top [7], natural convection	Ψ_{JT}	2	°C/W

1 Thermal characteristics are targets based on simulation that are subject to change per device characterization. This data is PRELIMINARY based on similar package used on other devices.

2 Junction temperature is a function of on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

3 Per SEMI G38-87 and JEDEC JESD51-2 with the single-layer board horizontal.

4 Per JEDEC JESD51-6 with the board horizontal.

5 Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.

package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm. of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

References:

Semiconductor Equipment and Materials International
3081 Zanker Road
San Jose, CA 95134
(408) 943-6900

MIL-SPEC and EIA/JESD (JEDEC) specifications are available from Global Engineering Documents at 800-854-7179 or 303-397-7956.

JEDEC specifications are available on the WEB at http://www.jedec.org.

- C.E. Triplett and B. Joiner, “An Experimental Characterization of a 272 PBGA Within an Automotive Engine Controller Module,” Proceedings of SemiTherm, San Diego, 1998, pp. 47-54.
- G. Kromann, S. Shidore, and S. Addison, “Thermal Modeling of a PBGA for Air-Cooled Applications,” Electronic Packaging and Production, pp. 53-58, March 1998.
- B. Joiner and V. Adams, “Measurement and Simulation of Junction to Board Thermal Resistance and Its Application in Thermal Modeling,” Proceedings of SemiTherm, San Diego, 1999, pp. 212-220.

4.3 EMI (Electromagnetic Interference) Characteristics

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions, go to www.freescale.com and perform a keyword search for “radiated emissions.” The following tables list the values of the device's radiated emissions operating behaviors.

Table 7. EMC Radiated Emissions Operating Behaviors: 416 BGA

Symbol	Description	Conditions	f_{OSC} f_{SYS}	Frequency band (MHz)	Level (max.)	Unit	Notes
V_{RE_TEM}	Radiated emissions, electric field and magnetic field	V_{DD} = 1.2 V V_{DDE} = 3.3 V V_{DDEH} = 5 V T_A = 25 °C 416 BGA EBI off CLK on FM off	40 MHz crystal 264 MHz (f_{EBI_CAL} = 66 MHz)	0.15–50	26	dBμV	1
				50–150	30		
				150–500	34		
				500–1000	30		
				IEC and SAE level	I[2]	—	1, 3
V_{RE_TEM}	Radiated emissions, electric field and magnetic field	V_{DD} = 1.2 V V_{DDE} = 3.3 V V_{DDEH} = 5 V T_A = 25 °C 416 BGA EBI off CLK off FM on[4]	40 MHz crystal 264 MHz (f_{EBI_CAL} = 66 MHz)	0.15–50	24	dBμV	1
				50–150	25		
				150–500	25		
				500–1000	21		
				IEC and SAE level	K[5]	—	1,3

1 Determined according to IEC Standard 61967-2, Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method, and SAE Standard J1752-3, Measurement of Radiated Emissions from Integrated Circuits—TEM/Wideband TEM (GTEM) Cell Method.

2 I = 36 dBμV

3 Specified according to Annex D of IEC Standard 61967-2, Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method, and Appendix D of SAE Standard J1752-3, Measurement of Radiated Emissions from Integrated Circuits—TEM/Wideband TEM (GTEM) Cell Method.

Table 14. DC Electrical Specifications (continued)

Spec	Characteristic	Symbol	Min	Max	Unit
27	Operating Current V_{DDE}/V_{DDEH}[17] Supplies V_{DDE2} V_{DDEH1} V_{DDEH3} V_{DDEH4} V_{DDEH5} V_{DDEH6} V_{DDEH7}	 I_{DD2} I_{DD1} I_{DD3} I_{DD4} I_{DD5} I_{DD6} I_{DD7}	 — — — — — — —	 note[17]	 mA mA mA mA mA mA mA
28	Fast I/O Weak Pull Up/Down Current[18] 3.0 V–3.6 V	 I_{ACT_F}	 42	 158	 µA
29	Medium I/O Weak Pull Up/Down Current[19] 3.0 V–3.6 V 4.5 V–5.5 V	I_{ACT_S}	 15 35	 95 200	 µA µA
30	I/O Input Leakage Current[20]	I_{INACT_D}	–2.5	2.5	µA
31	DC Injection Current (per pin)	I_{IC}	–1.0	1.0	mA
32	Analog Input Current, Channel Off[21], AN[0:7], AN38, AN39 Analog Input Current, Channel Off, all other analog inputs AN[x]	I_{INACT_A}	–250 –150	250 150	nA nA
33	V_{SS} Differential Voltage	$V_{SS} – V_{SSA}$	–100	100	mV
34	Analog Reference Low Voltage	V_{RL}	V_{SSA}	V_{SSA} + 100	mV
35	V_{RL} Differential Voltage	$V_{RL} – V_{SSA}$	–100	100	mV
36	Analog Reference High Voltage	V_{RH}	V_{DDA} – 100	V_{DDA}	mV
37	V_{REF} Differential Voltage	$V_{RH} – V_{RL}$	4.75	5.25	V
38	V_{SSSYN} to V_{SS} Differential Voltage	$V_{SSSYN} – V_{SS}$	–100	100	mV
39	Operating Temperature Range—Ambient (Packaged)	T_A (T_L to T_H)	–40.0	125.0	°C
40	Slew rate on power supply pins	—	—	25	V/ms
41	Weak Pull-Up/Down Resistance[22], 200 K Option	$R_{PUPD200K}$	130	280	kΩ
42	Weak Pull-Up/Down Resistance[22], 100 K Option	$R_{PUPD100K}$	65	140	kΩ
43	Weak Pull-Up/Down Resistance[22], 5 K Option	R_{PUPD5K}	1.4	7.5	kΩ
44	Pull-Up/Down Resistance Matching Ratios[23] (100K/200K)	$R_{PUPDMTCH}$	–2.5	+2.5	%

1 Voltage overshoots during a high-to-low or low-to-high transition must not exceed 10 seconds per instance.

2 2.0 V for 10 hours cumulative time, 1.2 V +10% for time remaining.

3 Assumed with DC load.

4 5.3 V for 10 hours cumulative time, 3.3 V +10% for time remaining.

5 6.4 V for 10 hours cumulative time, 5.0 V +10% for time remaining.

6 V_{STBY} below 0.95 V the RAM will not retain states, but will be operational. V_{STBY} can be 0 V when bypass standby mode.

7 Regulator is functional with derated performance, with supply voltage down to 4.0 V for system with V_{DDREG} = 4.5 V (min).

8 2.7 V minimum operating voltage allowed during vehicle crank for system with V_{DDREG} = 3.0 V (min). Normal operating voltage should be either V_{DDREG} = 3.0 V (min) or 4.5 V (min) depending on the user regulation voltage system selected.

9 Required to be supplied when 3.3 V regulator is disabled. See Section 4.5, “PMC/POR/LVI Electrical Specifications.”

4.11.2 Pad AC Specifications

Table 30. Pad AC Specifications (V_{DDEH} = 5.0 V, V_{DDE} = 3.3 V)[1]

Spec	Pad	SRC/DSC	Out Delay[2,4] L → H/H → L (ns)	Rise/Fall[3,4] (ns)	Load Drive (pF)
1	Medium[5]	00	152/165	70/74	50
2			205/220	96/96	200
3		01	28/34	12/15	50
4			52/59	28/31	200
5		11	12/12	5.3/5.9	50
6			32/32	22/22	200
7	Fast[5]	00	2.5	1.2	10
8		01			20
9		10			30
10		11			50
11	Fast with Slew Rate	00	40/40	16/16	50
12			50/50	21/21	200
13		01	13/13	5/5	50
14			19/19	8/8	200
15		10	8/8	2.4/2.4	50
16			12/12	5/5	200
17		11	5/5	1.1/1/1	50
18			8/8	2.6	2.6
19	Pull Up/Down (3.6 V max)	—	—	7500	50
20	Pull Up/Down (5.25 V max)	—	6000	5000/5000	50

1 These are worst case values that are estimated from simulation and not tested. The values in the table are simulated at V_{DD} = 1.02 V to 1.32 V, V_{DDE} = 3.0 V to 3.6 V, V_{DDEH} = 4.75 V to 5.25 V, V_{DD33} and V_{DDSYN} = 3.0 V to 3.6 V, $T_A = T_L$ to T_H.

2 This parameter is supplied for reference and is not guaranteed by design and not tested.

3 This parameter is guaranteed by characterization before qualification rather than 100% tested.

4 Delay and rise/fall are measured to 20% or 80% of the respective signal.

5 Out delay is shown in Figure 17. Add a maximum of one system clock to the output delay for delay with respect to system clock.

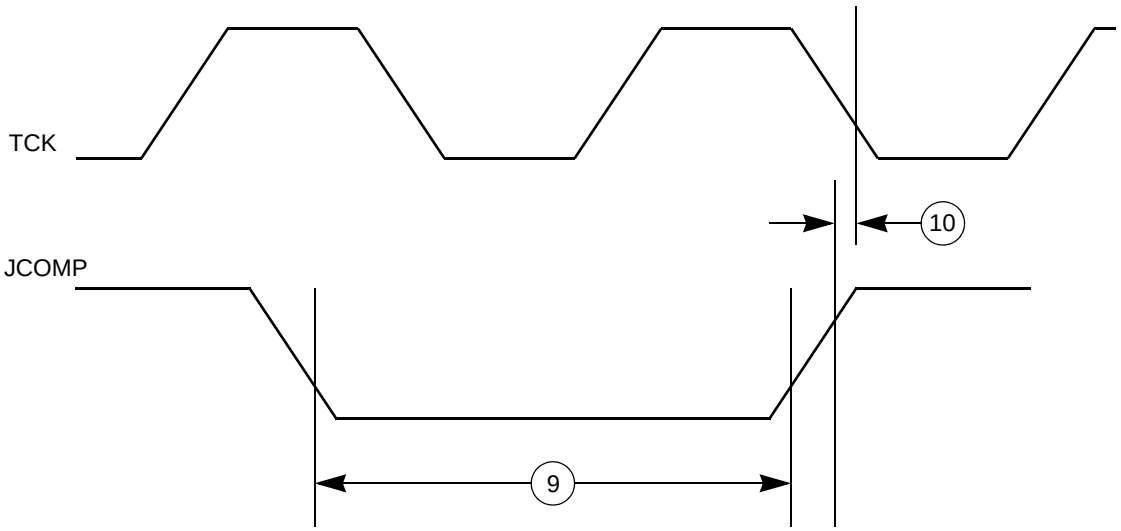


Figure 23. JTAG JCOMP Timing

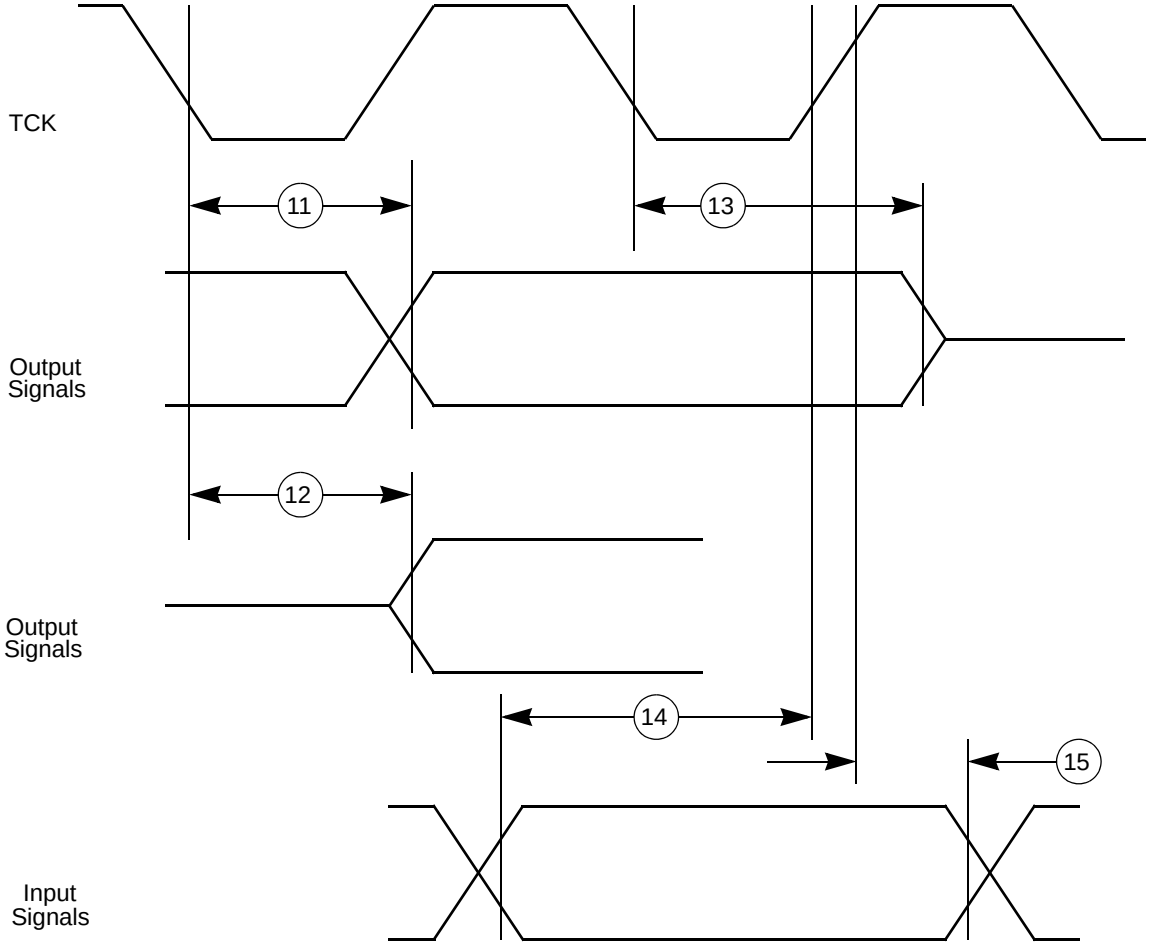


Figure 24. JTAG Boundary Scan Timing

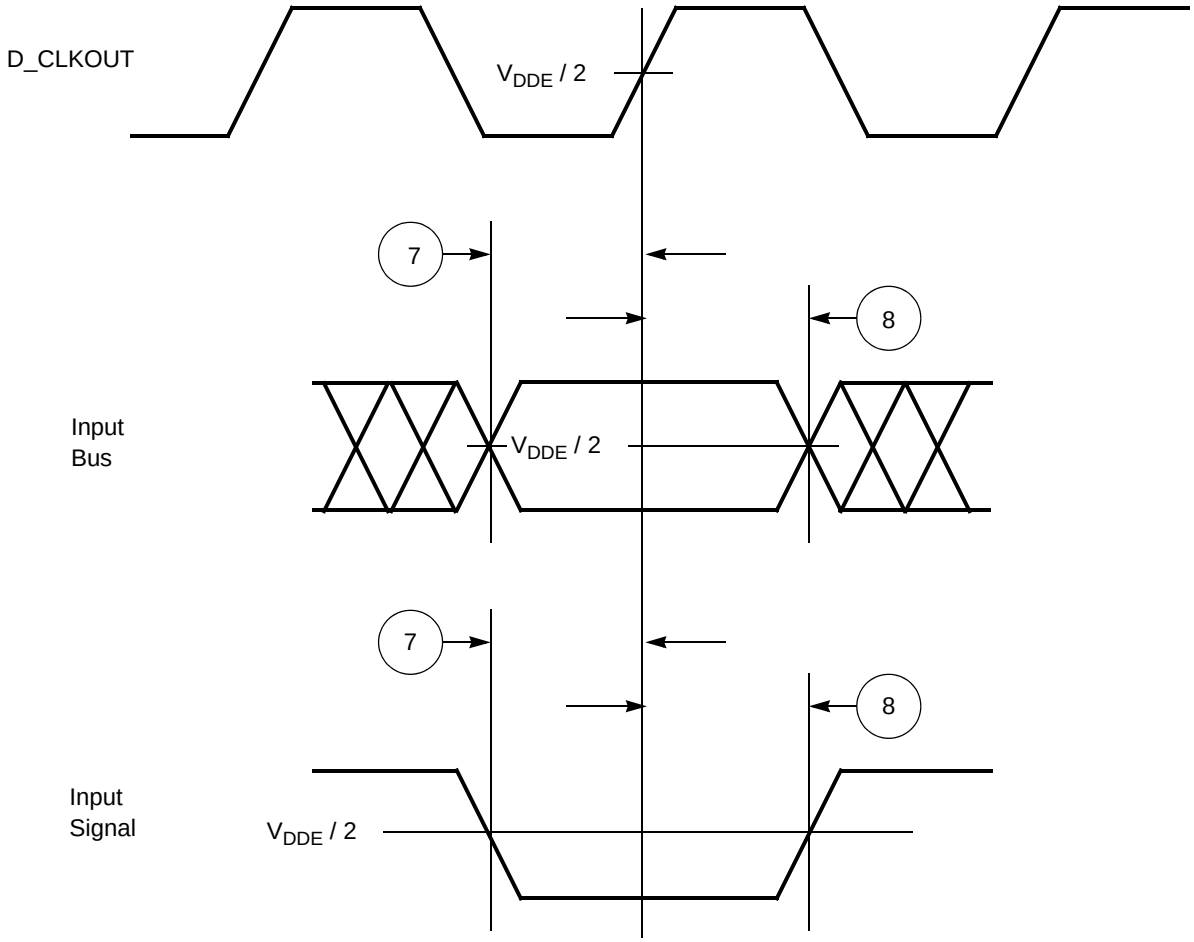


Figure 29. Synchronous Input Timing

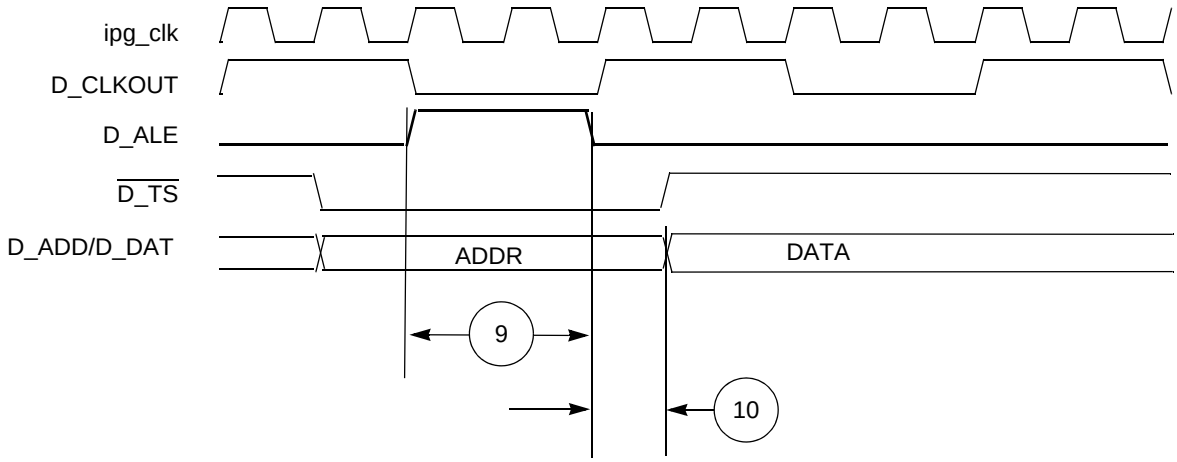


Figure 30. ALE Signal Timing

4.12.6 External Interrupt Timing (IRQ Pin)

Table 36. External Interrupt Timing[1]

Spec	Characteristic	Symbol	Min	Max	Unit
1	IRQ Pulse Width Low	t_{IPWL}	3	—	t_{cyc}[2]
2	IRQ Pulse Width High	t_{IPWH}	3	—	t_{cyc}[2]
3	IRQ Edge to Edge Time[3]	t_{ICYC}	6	—	t_{cyc}[2]

1 IRQ timing specified at V_{DD} = 1.08 V to 1.32 V, V_{DDEH} = 3.0 V to 5.5 V, V_{DD33} and V_{DDSYN} = 3.0 V to 3.6 V, $T_A = T_L$ to T_H.

2 See Notes on t_{cyc} on Figure 16 and Table 27 in Section 4.11.1, Clocking.

3 Applies when IRQ pins are configured for rising edge or falling edge events, but not both.

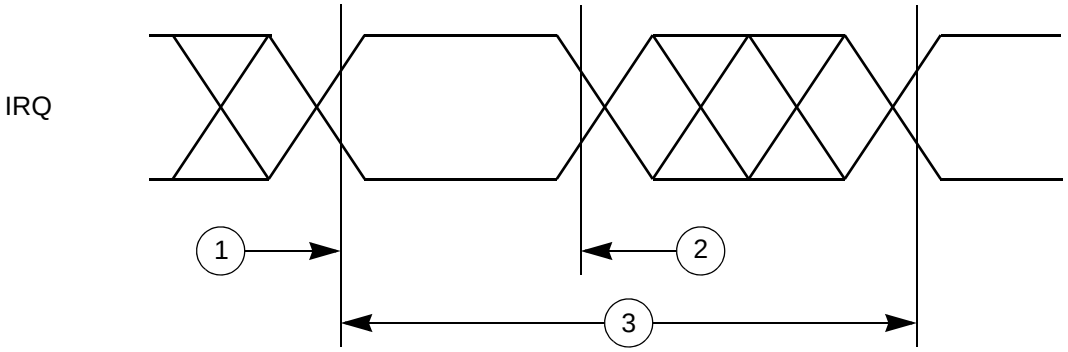


Figure 31. External Interrupt Timing

4.12.7 eTPU Timing

Table 37. eTPU Timing[1]

Spec	Characteristic	Symbol	Min	Max	Unit
1	eTPU Input Channel Pulse Width	t_{ICPW}	4	—	t_{cyc}[2]
2	eTPU Output Channel Pulse Width	t_{OCPW}	1[3]	—	t_{cyc}[2]

1 eTPU timing specified at V_{DD} = 1.08 V to 1.32 V, V_{DDEH} = 3.0 V to 5.5 V, V_{DD33} and V_{DDSYN} = 3.0 V to 3.6 V, $T_A = T_L$ to T_H, and C_L = 200 pF with SRC = 0b00.

2 See Notes on t_{cyc} on Figure 16 and Table 27 in Section 4.11.1, Clocking.

3 This specification does not include the rise and fall times. When calculating the minimum eTPU pulse width, include the rise and fall times defined in the slew rate control fields (SRC) of the pad configuration registers (PCR).

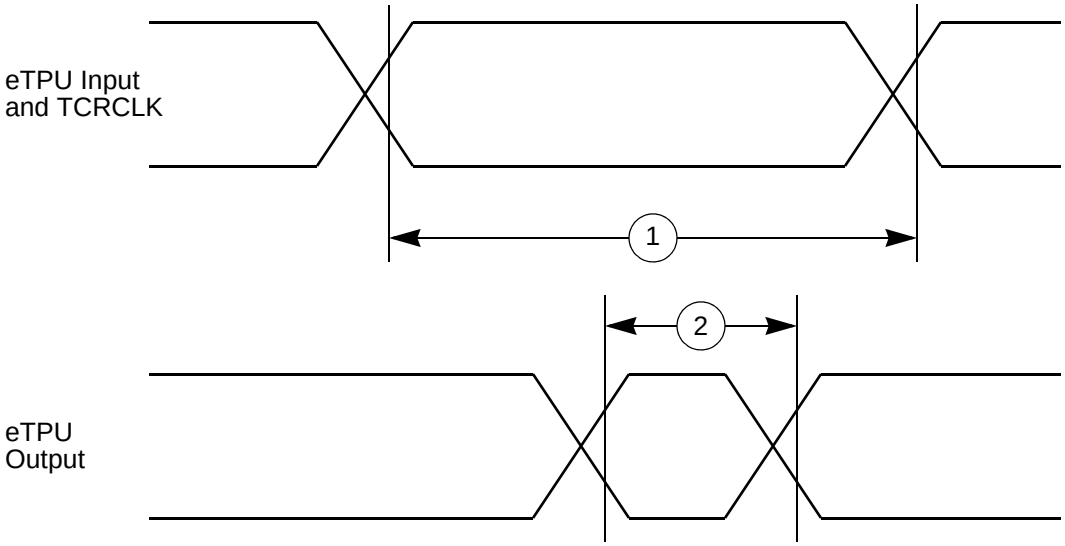


Figure 32. eTPU Timing

4.12.8 eMIOS Timing

Table 38. eMIOS Timing[1]

Spec	Characteristic	Symbol	Min	Max	Unit
1	eMIOS Input Pulse Width	t_{MIPW}	4	—	t_{cyc}[2]
2	eMIOS Output Pulse Width	t_{MOPW}	1[3]	—	t_{cyc}[2]

1 eMIOS timing specified at V_{DD} = 1.08 V to 1.32 V, V_{DDEH} = 3.0 V to 5.5 V, V_{DD33} and V_{DDSYN} = 3.0 V to 3.6 V, $T_A = T_L$ to T_H, and C_L = 50 pF with SRC = 0b00.

2 See Notes on t_{cyc} on Figure 16 and Table 27 in Section 4.11.1, Clocking.

3 This specification does not include the rise and fall times. When calculating the minimum eMIOS pulse width, include the rise and fall times defined in the slew rate control fields (SRC) of the pad configuration registers (PCR).

Figure 46. 416 TEPBGA Package (2 of 2)

Table 42. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
125	ETPUA11_ETPUA23_ GPIO125	P	ETPUA11	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	G2	H1	G1
		A1	ETPUA23	eTPU A channel (output only)	O							
		A2	—	—	—							
		G	GPIO125	GPIO	I/O							
126	ETPUA12_PCSB1_ GPIO126	P	ETPUA12	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	G3	H2	J5
		A1	PCSB1	DSPI B peripheral chip select	O							
		A2	—	—	—							
		G	GPIO126	GPIO	I/O							
127	ETPUA13_PCSB3_ GPIO127	P	ETPUA13	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	F1	H4	G2
		A1	PCSB3	DSPI B peripheral chip select	O							
		A2	—	—	—							
		G	GPIO127	GPIO	I/O							
128	ETPUA14_PCSB4_ GPIO128	P	ETPUA14	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	F2	H3	H5
		A1	PCSB4	DSPI B peripheral chip select	O							
		A2	—	—	—							
		G	GPIO128	GPIO	I/O							
129	ETPUA15_PCSB5_ GPIO129	P	ETPUA15	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	F3	G1	G3
		A1	PCSB5	DSPI B peripheral chip select	O							
		A2	—	—	—							
		G	GPIO129	GPIO	I/O							
130	ETPUA16_PCSD1_ GPIO130	P	ETPUA16	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	H4	G2	H6
		A1	PCSD1	DSPI D peripheral chip select	O							
		A2	—	—	—							
		G	GPIO130	GPIO	I/O							

Table 42. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
131	ETPUA17_PCSD2_ GPIO131	P	ETPUA17	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	G4	G3	G4
		A1	PCSD2	DSPI D peripheral chip select	O							
		A2	—	—	—							
		G	GPIO131	GPIO	I/O							
132	ETPUA18_PCSD3_ GPIO132	P	ETPUA18	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	—	G4	G5
		A1	PCSD3	DSPI D peripheral chip select	O							
		A2	—	—	—							
		G	GPIO132	GPIO	I/O							
133	ETPUA19_PCSD4_ GPIO133	P	ETPUA19	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	—	F1	F1
		A1	PCSD4	DSPI D peripheral chip select	O							
		A2	—	—	—							
		G	GPIO133	GPIO	I/O							
134	ETPUA20_IRQ8_ GPIO134	P	ETPUA20	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	E1	F2	F2
		A1	IRQ8	External interrupt request	I							
		A2	—	—	—							
		G	GPIO134	GPIO	I/O							
135	ETPUA21_IRQ9_ GPIO135	P	ETPUA21	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	C1	F3	F3
		A1	IRQ9	External interrupt request	I							
		A2	—	—	—							
		G	GPIO135	GPIO	I/O							
136	ETPUA22_IRQ10_ GPIO136	P	ETPUA22	eTPU A channel	I/O	MH	V_{DDEH1}	—/WKPCFG	—/WKPCFG	E2	F4	F4
		A1	IRQ10	External interrupt request	I							
		A2	—	—	—							
		G	GPIO136	GPIO	I/O							

Table 42. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
149	ETPUB2_ETPUB18_ GPIO149	P	ETPUB2	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	R22	T26	U23
		A1	ETPUB18	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO149	GPIO	I/O							
150	ETPUB3_ETPUB19_ GPIO150	P	ETPUB3	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	R21	R23	T22
		A1	ETPUB19	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO150	GPIO	I/O							
151	ETPUB4_ETPUB20_ GPIO151	P	ETPUB4	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	P22	R24	U24
		A1	ETPUB20	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO151	GPIO	I/O							
152	ETPUB5_ETPUB21_ GPIO152	P	ETPUB5	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	P21	R25	U25
		A1	ETPUB21	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO152	GPIO	I/O							
153	ETPUB6_ETPUB22_ GPIO153	P	ETPUB6	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	N22	R26	U26
		A1	ETPUB22	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO153	GPIO	I/O							
154	ETPUB7_ETPUB23_ GPIO154	P	ETPUB7	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	M19	P23	T23
		A1	ETPUB23	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO154	GPIO	I/O							

Table 42. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
161	ETPUB14_ETPUB30_ GPIO161	P	ETPUB14	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	L21	M25	R24
		A1	ETPUB30	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO161	GPIO	I/O							
162	ETPUB15_ETPUB31_ GPIO162	P	ETPUB15	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	—	M24	R25
		A1	ETPUB31	eTPU B channel (output only)	O							
		A2	—	—	—							
		G	GPIO162	GPIO	I/O							
163	ETPUB16_PCSA1_ GPIO163	P	ETPUB16	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	P20	U26	V24
		A1	PCSA1	DSPI A peripheral chip select	O							
		A2	—	—	—							
		G	GPIO163	GPIO	I/O							
164	ETPUB17_PCSA2_ GPIO164	P	ETPUB17	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	R20	U25	T21
		A1	PCSA2	DSPI A peripheral chip select	O							
		A2	—	—	—							
		G	GPIO164	GPIO	I/O							
165	ETPUB18_PCSA3_ GPIO165	P	ETPUB18	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	T20	U24	W26
		A1	PCSA3	DSPI A peripheral chip select	O							
		A2	—	—	—							
		G	GPIO165	GPIO	I/O							
166	ETPUB19_PCSA4_ GPIO166	P	ETPUB19	eTPU B channel	I/O	MH	V_{DDEH6}	—/WKPCFG	—/WKPCFG	T19	U23	W25
		A1	PCSA4	DSPI A peripheral chip select	O							
		A2	—	—	—							
		G	GPIO166	GPIO	I/O							

Table 42. Signal Properties and Muxing Summary (continued)

GPIO/PCR[1]	Signal Name[2]	P/A/G[3]	Function[4]	Function Summary	Direction	Pad Type[5]	Voltage[6]	State during RESET[7]	State after RESET[8]	Package Location		
										324	416	516
188	EMIOS9_ETPUA9_ GPIO188	P	EMIOS9	eMIOS channel	I/O	MH	V_{DDEH4}	—/WKPCFG	—/WKPCFG	W11	AD13	AF15
		A1	ETPUA9	eTPU A channel	O							
		A2	—	—	—							
		G	GPIO188	GPIO	I/O							
189	EMIOS10_SCKD_ GPIO189	P	EMIOS10	eMIOS channel	I/O	MH	V_{DDEH4}	—/WKPCFG	—/WKPCFG	AA11	AE13	AE15
		A1	SCKD	DSPI D clock	O							
		A2	—	—	—							
		G	GPIO189	GPIO	I/O							
190	EMIOS11_SIND_ GPIO190	P	EMIOS11	eMIOS channel	I/O	MH	V_{DDEH4}	—/WKPCFG	—/WKPCFG	AB12	AF13	AB14
		A1	SIND	DSPI D data input	I							
		A2	—	—	—							
		G	GPIO190	GPIO	I/O							
191	EMIOS12_SOUTC_ GPIO191	P	EMIOS12	eMIOS channel	O	MH	V_{DDEH4}	—/WKPCFG	—/WKPCFG	AB13	AF14	AD15
		A1	SOUTC	DSPI C data output	O							
		A2	—	—	—							
		G	GPIO191	GPIO	I/O							
192	EMIOS13_SOUTD_ GPIO192	P	EMIOS13	eMIOS channel	O	MH	V_{DDEH4}	—/WKPCFG	—/WKPCFG	AA12	AE14	AC15
		A1	SOUTD	DSPI D data output	O							
		A2	—	—	—							
		G	GPIO192	GPIO	I/O							
193	EMIOS14_IRQ0_ GPIO193	P	EMIOS14	eMIOS channel	O	MH	V_{DDEH4}	—/WKPCFG	—/WKPCFG	Y12	AC14	AF17
		A1	IRQ0	External interrupt request	I							
		A2	CNTXD	FlexCAN D transmit	O							
		G	GPIO193	GPIO	I/O							

Table 43 lists the pin locations of the power and ground signals on the 324 TEPBGA package.

Table 43. 324-pin Power Supply Locations

VDD

A2	B3	C4	D5	K3	V19	W5	W9	W20	Y4	Y21	AA3	AA22	AB2

VDD33

W21	V4

VDDE2

AB4	M9	N1	N10	N9	P10	P9	T4	W6	V2

VDDEH1

B1	L4

VDDEH4

AB20	W8

VDDEH6

N20	T21

VDDEH7

C22	H19	L22

VSS

A1	A22	AA2	AA21	AB1	AB22	B2	B21	C20	C3	D19	D4	J10	J11	J12	J13	J14	J9
K10	K11	K12	K13	K14	K9	L10	L11	L12	L13	L14	L9	M10	M11	M12	M13	M14	N11
N12	N13	N14	P11	P12	P13	P14	W19	W4	Y20	Y3							

Table 44 lists the pin locations of the power and ground signals on the 416 TEPBGA package.

Table 44. 416-pin Power Supply Locations

VDD

A2	B3	C4	D5	N4	AB4	AB23	AC3	AC12	AC24	AD2	AD25	AE1	AE26

VDD33

M1	AA4	AA23

VDDE2

N10	P10	P11	R10	R11	T1	T10	T11	T12	U10	U11	U12	W4	AC1	AC5	AF2

VDDEH1

B1	P4

VDDEH3

AC10	AF5

VDDEH4

AC11	AF22

VDDEH5

AC21	AF25

VDDEH6

N23	AC25

VDDEH7

D24	E23	M26

VSS

A1	A26	B2	B25	C3	C24	D4	D23	K10	K11	K12	K13	K14	K15	K16	K17	L10	L11
L12	L13	L14	L15	L16	L17	M10	M11	M12	M13	M14	M15	M16	M17	N11	N12	N13	N14
N15	N16	N17	P12	P13	P14	P15	P16	P17	R12	R13	R14	R15	R16	R17	T13	T14	T15
T16	T17	U13	U14	U15	U16	U17	AC4	AC23	AD3	AD24	AE2	AE25	AF1	AF26			

Table 46. Revision History (continued)

Revision (Date)	Description of changes
	Updated Table 3, “Absolute Maximum Ratings” with the following: - Spec 1, ‘1.2 V Core Supply Voltage’, to a Max of 2.0 V - Spec 3, ‘Clock Synthesizer Voltage’, to a Max of 5.3 V - Spec 4, ‘I/O Supply Voltage’ to a Max of 5.3 V - Spec 5, ‘Analog Supply Voltage’ to a Max of 5.3 V - Note 2 to read, “2.0 V for 10 hours cumulative time, 1.32 V +10% for time remaining.“ - Note 3, “... 5.0 V + 10% ...” to “... 5.25 V + 10 % ...” - Note 5, “... 3.3 V + 10% ...” to “... 3.60 V + 10 % ...” Updated Spec 2 (ESD for Charged Device Model (CDM)) of Table 9, “ESD Ratings”, to 500 V Updated Table 27, “PFCPR1 Settings vs. Frequency of Operation“, Spec 3, APC = RWSC column to 0b100. Updated Spec 26, “Operating Current 5.0 V Supplies @ f_{sys} = 264 MHz“ for I_{DDA} to 50 mA, in Table 14, “DC electrical specifications”.